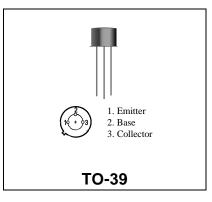


MS1649

RF & MICROWAVE TRANSISTORS UHF CLASS C MOBILE APPLICATIONS

Features

- 470 MHz
- **P**_{OUT} = 3W
- $G_P = 9.5 dB MINIMUM$
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1649 is a 12.5V epitaxial NPN planar transistor designed primarily for UHF communications. This device is packaged in a grounded emitter TO-39 package for increased power gain and optimum heat dissipation.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol Parameter		Value	Unit	
V _{сво}	Collector-Base Voltage	36	V	
V _{CEO}	Collector-Emitter Voltage	16	V	
V _{EBO}	Emitter-Base Voltage	3.5	V	
Ι _C	Collector Current	1.0	Α	
Ρτοτ	Total Power Dissipation	7.8	W	
T _{STG}	Storage Temperature	-65 to +200	°C	
ТJ	Junction Temperature	+200	°C	

Thermal Data

R _{TH(J-C)} Thermal Resistance Junction-Case	35.0	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			
			Min.	Тур.	Max.	Unit
BV _{CES}	I _c = 50mA	V _{BE} = 0	36			V
BV _{CEO}	I _c = 50mA	I _B = 0	16			V
\mathbf{BV}_{EBO}	I _E = 1mA	$I_{\rm C} = 0$	3.5			V
I _{CES}	V _{CB} = 12.5V	V _{BE} = 0			1.0	mA
H _{FE}	V _{CE} = 5.0V	I _c =100mA	20		150	

DYNAMIC

Symbol		Test Conditions	5		Value		
				Min.	Тур.	Max.	Unit
G _{PE}	f = 470MHz	P _{OUT} = 3.0W	V _{CC} = 12.5V	9.5			dB
η	f = 470MHz	P _{OUT} = 3.0W	V _{CC} = 12.5V	50			%
Сов	f = 1.0MHz	V _{CB} = 12.5 V				12	pf

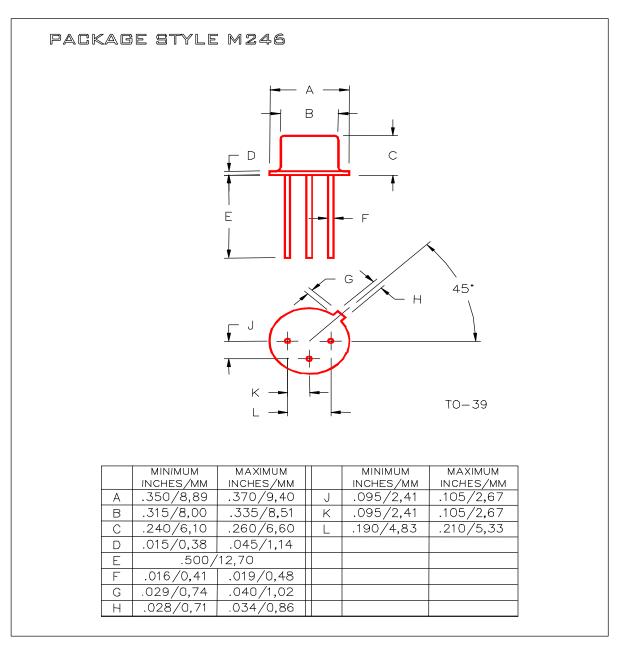
IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$		
175 MHz	3.5 + j1.2	14.0 + j10.0		
470 MHz	3.3 + j3.2	11.0 + j5.7		



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PACKAGE MECHANICAL DATA



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